

PTO-1449		Application No. 10/663,051		Applicant(s): GORDON MA ET AL.	
Information Disclosure Citation in an Application		Docket Number 068736.0232		Group Art Unit 2811	Filing Date September 15, 2003

**U.S. PATENT DOCUMENTS**

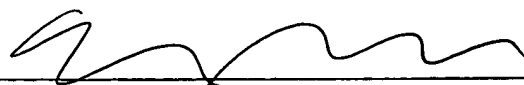
	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
EL	1	4,811,075	03/07/89	Eklund	357	46	04/24/87
EL	2	5,155,563	10/13/92	Davies et al.	357	23.4	03/18/91
EL	3	5,313,082	05/17/94	Eklund	257	262	02/16/93
EL	4	6,168,983	01/02/01	Rumennik et al.	438	188	02/05/99
EL	5	6,563,171	05/13/03	Disney	257	342	11/12/02

**FOREIGN PATENT DOCUMENTS**

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

**NON-PATENT DOCUMENTS**

	DOCUMENT (Including Author, Title, Source, and Pertinent Pages)	DATE
EL	6 J.A. Appels and H.M.J. Vaes, "High voltage thin layer devices (RESURF devices)", IEDM technical digest, pp. 238-241	1979
EL	7 H.M.J. Vaes and J.A. Appels, "High voltage high current lateral devices", IEDM technical digest, pp. 87-90	1980
EL	8 T. Fujihira, "Theory of Semiconductor Superjunction Devices", Jpn. J. Appl. Phys., vol. 36, pp. 6254-6262	1997
EL	9 G. Deboy, M. Marz, J.-P. Stengl, H. Strack, J. Tihanyi and H. Weber, "A new generation of high voltage MOSFETs breaks the limit line of silicon", IEDM technical digest, pp. 683-685	1998
EL	10 A. Ludikhuizen, "A review of RESURF technology", Proc. of ISPSD, p. 11	2000
EL	11 J. Cai, C. Ren, N. Balasubramanian and J.K.O. Sin, "A novel high performance stacked LDD RF LDMOSFET, IEEE Electron Device Lett., vol. 22, no. 5, pp. 236-238	2001
EL	12 J.G. Mena and C.A.T. Salama, "High voltage multiple-resistivity Drift-Region LDMOS", Solid State Electronics, Vol. 29, No. 6, pp. 647-656	1986
EL	13 M.D. Pocha and R.W. Dutton, "A computer-aided design model for High-Voltage Double Diffused MOS (DMOS) Transistors", IEEE Journal of Solid-State Circuits, Vol. SC-11, No. 5	1976
EL	14 I. Yoshia, M. Katsueda, S. Ohtaka, Y. Maruyama and T. Okabe, "High Efficient 1.5 GHz Si Power MOSFET for Digital Cellular Front End"; Proceedings of International Symposium on Power Semiconductor Devices & ICs; Tokyo, pp. 156-157	1992

EXAMINER	DATE CONSIDERED
	8/28/07

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.